



PRODUCT DATA SHEET



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Datasheet



Resources



Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	190mΩ@4.5V	0.75A
	260mΩ@2.5V	
	390mΩ@1.8V	

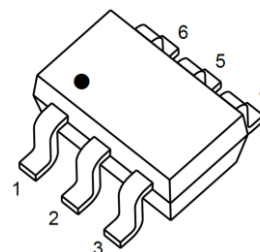
Feature

- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

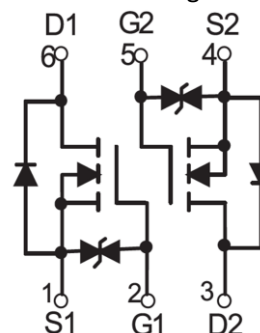
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

SOT-363



Schematic diagram


ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ⁽¹⁾	I_D	0.75	A
Power Dissipation ⁽¹⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

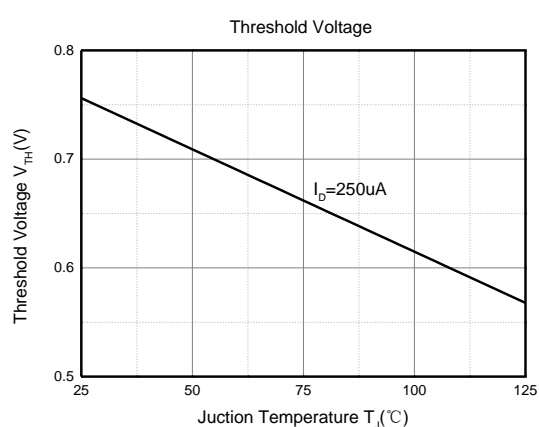
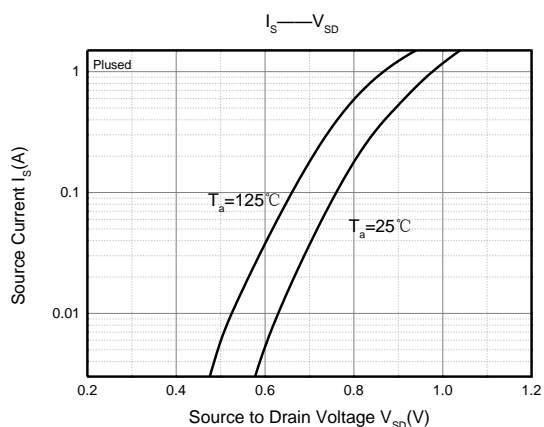
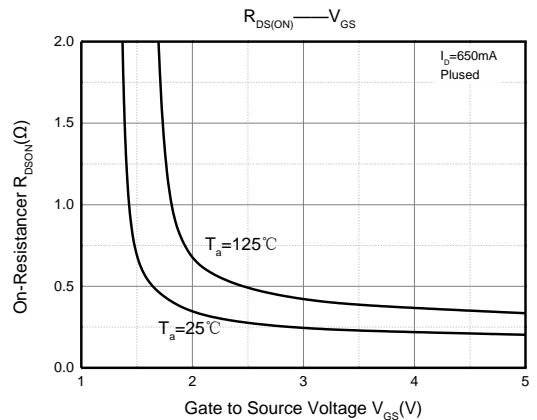
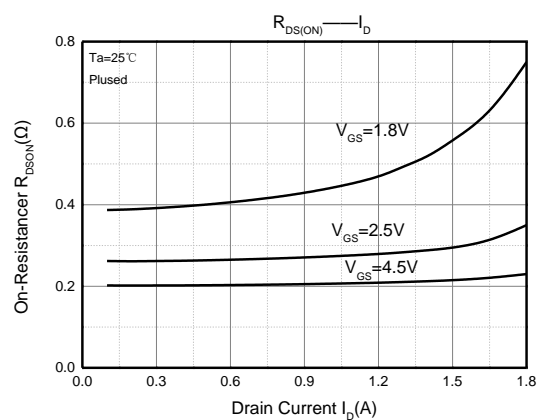
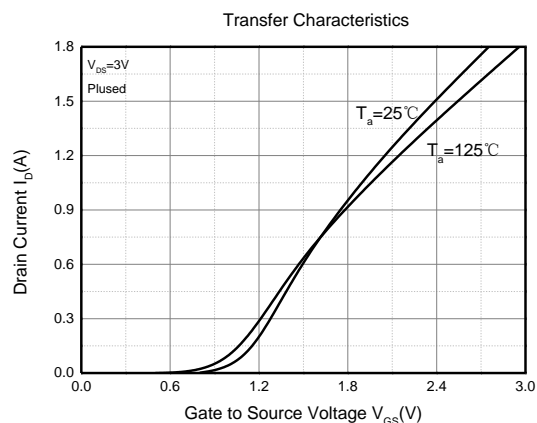
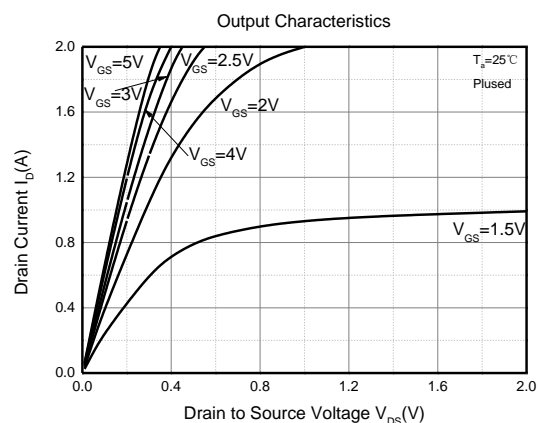
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

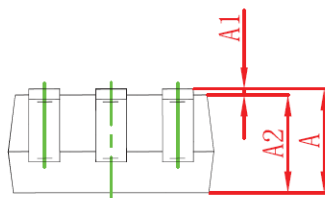
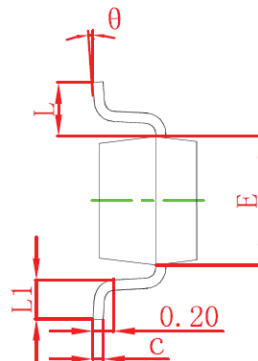
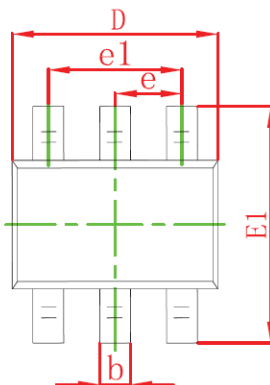
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =20V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage ⁽¹⁾	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.35	0.75	1.1	V
Drain-source on-resistance ⁽¹⁾	R _{DS(on)}	V _{GS} =4.5V, I _D =650mA		190	260	mΩ
		V _{GS} =2.5V, I _D =550mA		260	360	
		V _{GS} =1.8V, I _D =450mA		390	590	
Forward tranconductance ⁽¹⁾	g _{FS}	V _{DS} =10V, I _D =800mA		1.6		S
Dynamic characteristics ⁽²⁾						
Input Capacitance	C _{iss}	V _{DS} =16V, V _{GS} =0V, f=1MHz			120	pF
Output Capacitance	C _{oss}				20	
Reverse Transfer Capacitance	C _{rss}				15	
Switching Characteristics ⁽²⁾						
Turn-on delay time	t _{d(on)}	V _{DS} =10V, I _D =500mA, V _{GS} =4.5V, R _G =10Ω		6.7		ns
Turn-on rise time	t _r			4.8		
Turn-off delay time	t _{d(off)}			17.3		
Turn-off fall time	t _f			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽¹⁾	V _{DS}	I _S =0.15A, V _{GS} = 0V			1.2	V

Notes:

1. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 0.5%.
2. Guaranteed by design, not subject to production testing

Typical Electrical and Thermal Characteristics



SOT-363 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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